High-Side Measurement Current-Shunt Monitor with Open-Drain Comparator and Reference

Check for Samples: INA200, INA201, INA202

FEATURES

- **COMPLETE CURRENT SENSE SOLUTION**
- **0.6V INTERNAL VOLTAGE REFERENCE**
- **INTERNAL OPEN-DRAIN COMPARATOR**
- **LATCHING CAPABILITY ON COMPARATOR**
- **COMMON-MODE RANGE: –16V to +80V**
- **HIGH ACCURACY: 3.5% MAX ERROR OVER TEMPERATURE**
- **BANDWIDTH: 500kHz (INA200)**
- **QUIESCENT CURRENT: 1800μA (max)**
- **PACKAGES: SO-8, MSOP-8**

APPLICATIONS

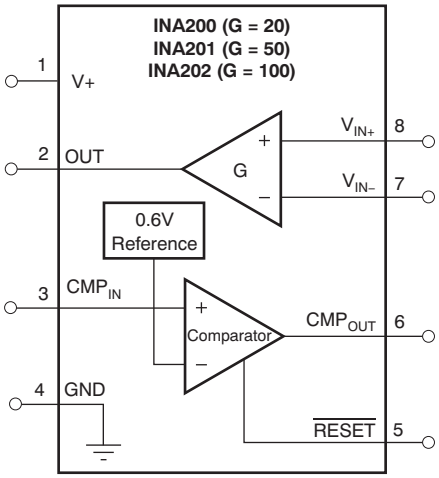
- **NOTEBOOK COMPUTERS**
- **CELL PHONES**
- **TELECOM EQUIPMENT**
- **AUTOMOTIVE**
- **POWER MANAGEMENT**
- **BATTERY CHARGERS**
- **WELDING EQUIPMENT**

DESCRIPTION

The INA200, INA201, and INA202 are high-side current-shunt monitors with voltage output. The INA200–INA202 can sense drops across shunts at common-mode voltages from –16V to 80V. The INA200–INA202 are available with three output voltage scales: 20V/V, 50V/V, and 100V/V, with up to 500kHz bandwidth.

The INA200, INA201, and INA202 also incorporate an open-drain comparator and internal reference providing a 0.6V threshold. External dividers are used to set the current trip point. The comparator includes a latching capability, which can be made transparent by grounding (or leaving open) the $\overline{\text{RESET}}$ pin.

The INA200, INA201, and INA202 operate from a single +2.7V to +18V supply, drawing a maximum of 1800μA of supply current. Package options include the very small MSOP-8 and the SO-8. All versions are specified over the extended operating temperature range of –40°C to +125°C.



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

ORDERING INFORMATION(1)

PRODUCT	GAIN	PACKAGE-LEAD	PACKAGE DESIGNATOR	PACKAGE MARKING
INA200	20V/V	MSOP-8	DGK	BQH
		SO-8	D	INA200A
INA201	50V/V	MSOP-8	DGK	BQJ
		SO-8	D	INA201A
INA202	100V/V	MSOP-8	DGK	BQL
		SO-8	D	INA202A

(1) For the most current package and ordering information see the Package Option Addendum at the end of this document, or see the device product folder at www.ti.com.

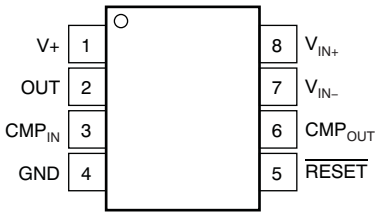
ABSOLUTE MAXIMUM RATINGS(1)

		VALUE	UNIT
Supply Voltage, V+		18	V
Current-Shunt Monitor Analog Inputs, V_{IN+}, V_{IN-}			
Differential (V_{IN+}) – (V_{IN-})		–18 to +18	V
Common Mode(2)		–16 to +80	V
Comparator Analog Input and Reset Pins(2)		GND – 0.3 to (V+) + 0.3	V
Analog Output, Out(2)		GND – 0.3 to (V+) + 0.3	V
Comparator Output, Out Pin(2)		GND – 0.3 to 18	V
Input Current Into Any Pin(2)		5	mA
Operating Temperature		–55 to +150	°C
Storage Temperature		–65 to +150	°C
Junction Temperature		+150	°C
ESD Ratings	Human Body Model (HBM)	4000	V
	Charged Device Model (CDM)	1000	V

(1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not supported.
(2) This voltage may exceed the ratings shown if the current at that pin is limited to 5mA.

PIN CONFIGURATIONS

INA200-INA202



MSOP-8 (DGK),
SO-8 (D)

ELECTRICAL CHARACTERISTICS: CURRENT-SHUNT MONITOR

Boldface limits apply over the specified temperature range: **T_A = –40°C to +125°C.**
At T_A = +25°C, V_S = +12V, V_{CM} = +12V, V_{SENSE} = 100mV, R_L = 10kΩ to GND, $R_{PULL-UP}$ = 5.1kΩ connected from CMP_{OUT} to V_S, and CMP_{IN} = GND, unless otherwise noted.

CURRENT-SHUNT MONITOR PARAMETERS		CONDITIONS	INA200, INA201, INA202			UNIT
			MIN	TYP	MAX	
INPUT						
Full-Scale Sense Input Voltage	V_{SENSE}	$V_{SENSE} = V_{IN+} - V_{IN-}$		0.15	$(V_S - 0.25)$/Gain	V
Common-Mode Input Range	**V_{CM}**		**–16**		**80**	**V**
Common-Mode Rejection	CMR	V_{IN+} = –16V to +80V	80	100		dB
Over Temperature		**V_{IN+} = +12V to +80V**	**100**	**123**		**dB**
Offset Voltage, RTI[1]	V_{OS}			±0.5	±2.5	mV
+25°C to +125°C					±3	mV
–40°C to +25°C					±3.5	mV
vs Temperature	**dV_{OS}/dT**	**T_{MIN} to T_{MAX}**		**5**		**µV/°C**
vs Power Supply	**PSR**	**V_{OUT} = 2V, V_{IN+} = +18V, 2.7V**		**2.5**	**100**	**µV/V**
Input Bias Current, V_{IN-} Pin	**I_B**			**±9**	**±16**	**µA**
OUTPUT (V_{SENSE} ≥ 20mV)						
Gain:	G					
INA200				20		V/V
INA201				50		V/V
INA202				100		V/V
Gain Error		V_{SENSE} = 20mV to 100mV		±0.2	±1	%
Over Temperature		**V_{SENSE} = 20mV to 100mV**			**±2**	**%**
Total Output Error[2]		V_{SENSE} = 120mV, V_S = +16V		±0.75	±2.2	%
Over Temperature		**V_{SENSE} = 120mV, V_S = +16V**			**±3.5**	**%**
Nonlinearity Error[3]		V_{SENSE} = 20mV to 100mV		±0.002		%
Output Impedance	R_O			1.5		Ω
Maximum Capacitive Load		No Sustained Oscillation		10		nF
OUTPUT (V_{SENSE} < 20mV)[4]						
INA200, INA201, INA202		–16V ≤ V_{CM} < 0V		300		mV
INA200		0V ≤ V_{CM} ≤ V_S, V_S = 5V			0.4	V
INA201		0V ≤ V_{CM} ≤ V_S, V_S = 5V			1	V
INA202		0V ≤ V_{CM} ≤ V_S, V_S = 5V			2	V
INA200, INA201, INA202		V_S < V_{CM} ≤ 80V		300		mV
VOLTAGE OUTPUT[5]						
Output Swing to the Positive Rail		**V_{IN-} = 11V, V_{IN+} = 12V**		**(V+) – 0.15**	**(V+) – 0.25**	**V**
Output Swing to GND[6]		**V_{IN-} = 0V, V_{IN+} = –0.5V**		**(V_{GND}) + 0.004**	**(V_{GND}) + 0.05**	**V**
FREQUENCY RESPONSE						
Bandwidth:	BW					
INA200		C_{LOAD} = 5pF		500		kHz
INA201		C_{LOAD} = 5pF		300		kHz
INA202		C_{LOAD} = 5pF		200		kHz
Phase Margin		C_{LOAD} < 10nF		40		Degrees
Slew Rate	SR			1		V/µs
Settling Time (1%)		V_{SENSE} = 10mV_{PP} to 100mV_{PP}, C_{LOAD} = 5pF		2		µs
NOISE, RTI						
Voltage Noise Density				40		nV/√Hz

(1) Offset is extrapolated from measurements of the output at 20mV and 100mV V_{SENSE}.
(2) Total output error includes effects of gain error and V_{OS}.
(3) Linearity is best fit to a straight line.
(4) For details on this region of operation, see the Accuracy Variations section in the Applications Information.
(5) See Typical Characteristic curve *Output Swing vs Output Current*.
(6) Specified by design.

ELECTRICAL CHARACTERISTICS: COMPARATOR

Boldface limits apply over the specified temperature range: **T_A = –40°C to +125°C.**
At T_A = +25°C, V_S = +12V, V_{CM} = +12V, V_{SENSE} = 100mV, R_L = 10kΩ to GND, and $R_{PULL-UP}$ = 5.1kΩ connected from CMP_{OUT} to V_S, unless otherwise noted.

COMPARATOR PARAMETERS		CONDITIONS	INA200, INA201, INA202			UNIT
			MIN	TYP	MAX	
OFFSET VOLTAGE						
Threshold		T_A = +25°C	590	608	620	mV
Over Temperature			**586**		**625**	**mV**
Hysteresis(1)		T_A = –40°C to +85°C		–8		mV
INPUT BIAS CURRENT(2)						
CMP_{IN} Pin				0.005	10	nA
vs Temperature					**15**	**nA**
INPUT VOLTAGE RANGE						
CMP_{IN} Pin				0V to V_S – 1.5V		V
OUTPUT (OPEN-DRAIN)						
Large-Signal Differential Voltage Gain		CMP V_{OUT} 1V to 4V, R_L ≥ 15kΩ Connected to 5V		200		V/mV
High-Level Leakage Current(3) (4)	I_{LKG}	V_{ID} = 0.4V, V_{OH} = V_S		0.0001	1	µA
Low-Level Output Voltage(3)	V_{OL}	V_{ID} = –0.6V, I_{OL} = 2.35mA		220	300	mV
RESPONSE TIME						
Response Time(5)		R_L to 5V, C_L = 15pF, 100mV Input Step with 5mV Overdrive		1.3		µs
$\overline{\text{RESET}}$						
$\overline{\text{RESET}}$ Threshold(6)				1.1		V
Logic Input Impedance				2		MΩ
Minimum $\overline{\text{RESET}}$ Pulse Width				1.5		µs
$\overline{\text{RESET}}$ Propagation Delay				3		µs

(1) Hysteresis refers to the threshold (the threshold specification applies to a rising edge of a noninverting input) of a falling edge on the noninverting input of the comparator; refer to Figure 1.
(2) Specified by design.
(3) V_{ID} refers to the differential voltage at the comparator inputs.
(4) Open-drain output can be pulled to the range of +2.7V to +18V, regardless of V_S.
(5) The comparator response time specified is the interval between the input step function and the instant when the output crosses 1.4V.
(6) The $\overline{\text{RESET}}$ input has an internal 2MΩ (typical) pull-down. Leaving $\overline{\text{RESET}}$ open results in a LOW state, with transparent comparator operation.

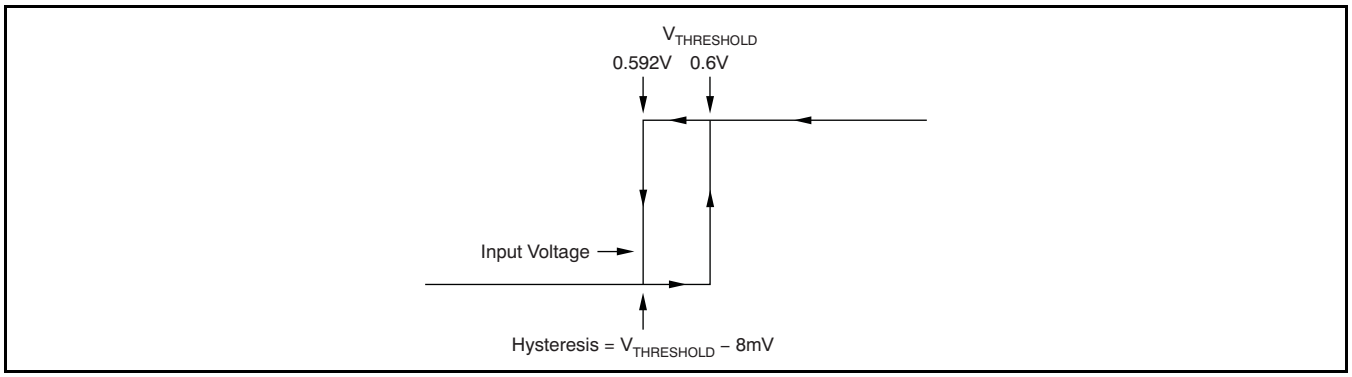


Figure 1. Typical Comparator Hysteresis

ELECTRICAL CHARACTERISTICS: GENERAL

Boldface limits apply over the specified temperature range: **T_A = –40°C to +125°C.**
At T_A = +25°C, V_S = +12V, V_{CM} = +12V, V_{SENSE} = 100mV, R_L = 10kΩ to GND, $R_{PULL-UP}$ = 5.1kΩ connected from CMP_{OUT} to V_S, and CMP_{IN} = 1V, unless otherwise noted.

GENERAL PARAMETERS		CONDITIONS	INA200, INA201, INA202			UNIT
			MIN	TYP	MAX	
POWER SUPPLY						
Operating Power Supply	**V_S**		**+2.7**		**+18**	**V**
Quiescent Current	I_Q	V_{OUT} = 2V		1350	1800	μA
Over Temperature		**V_{SENSE} = 0mV**			**1850**	**μA**
Comparator Power-On Reset Threshold(1)				1.5		V
TEMPERATURE						
Specified Temperature Range			–40		+125	°C
Operating Temperature Range			–55		+150	°C
Storage Temperature Range			–65		+150	°C
Thermal Resistance	θ_{JA}					
MSOP-8 Surface-Mount				200		°C/W
SO-8				150		°C/W

(1) The INA200, INA201, and INA202 are designed to power-up with the comparator in a defined reset state as long as $\overline{RESET}$ is open or grounded. The comparator is in reset as long as the power supply is below the voltage shown here. The comparator assumes a state based on the comparator input above this supply voltage. If $\overline{RESET}$ is high at power-up, the comparator output comes up high and requires a reset to assume a low state, if appropriate.

TYPICAL CHARACTERISTICS

At T_A = +25°C, V_S = +12V, V_{IN+} = 12V, and V_{SENSE} = 100mV, unless otherwise noted.

GAIN vs FREQUENCY

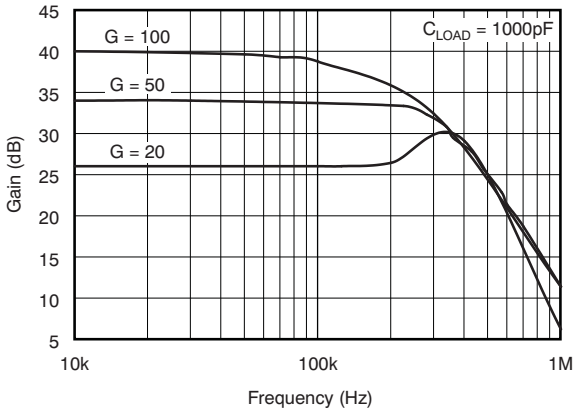


Figure 2.

GAIN vs FREQUENCY

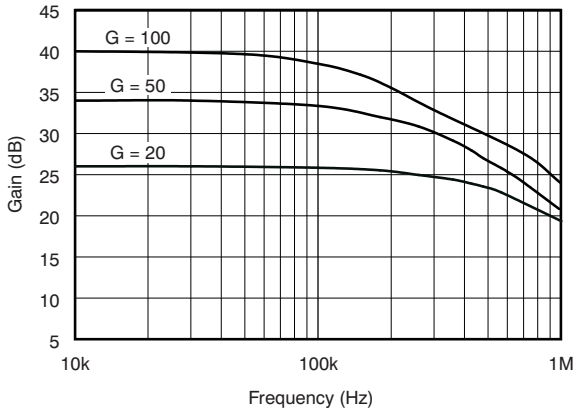


Figure 3.

GAIN PLOT

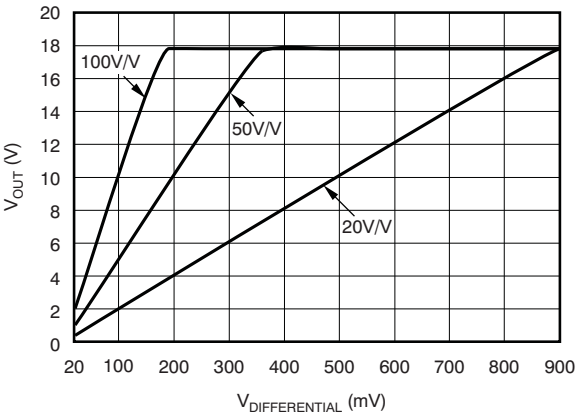


Figure 4.

COMMON-MODE AND POWER-SUPPLY REJECTION vs FREQUENCY

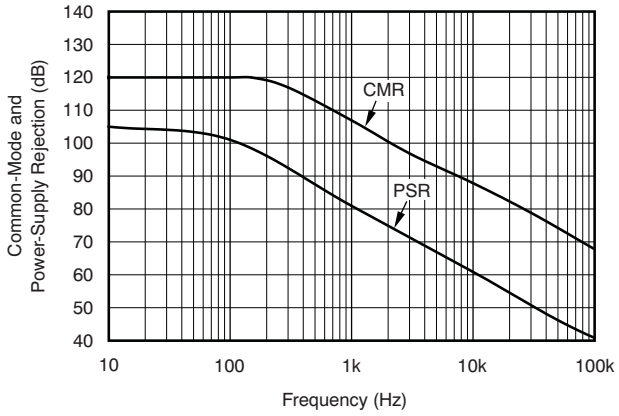


Figure 5.

OUTPUT ERROR vs V_{SENSE}

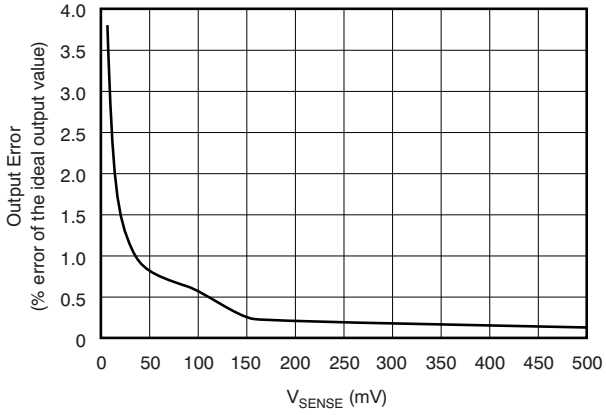


Figure 6.

OUTPUT ERROR vs COMMON-MODE VOLTAGE

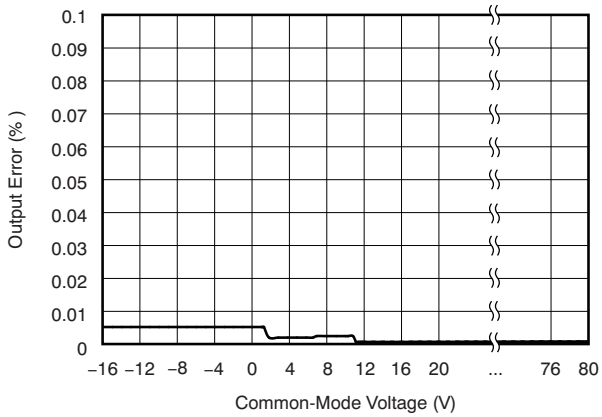


Figure 7.

TYPICAL CHARACTERISTICS (continued)

At T_A = +25°C, V_S = +12V, V_{IN+} = 12V, and V_{SENSE} = 100mV, unless otherwise noted.

POSITIVE OUTPUT VOLTAGE SWING vs OUTPUT CURRENT

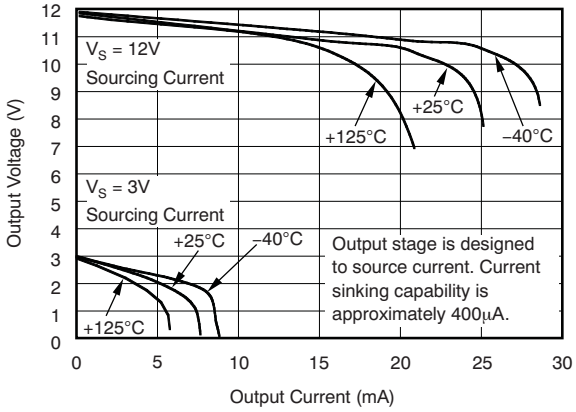


Figure 8.

QUIESCENT CURRENT vs OUTPUT VOLTAGE

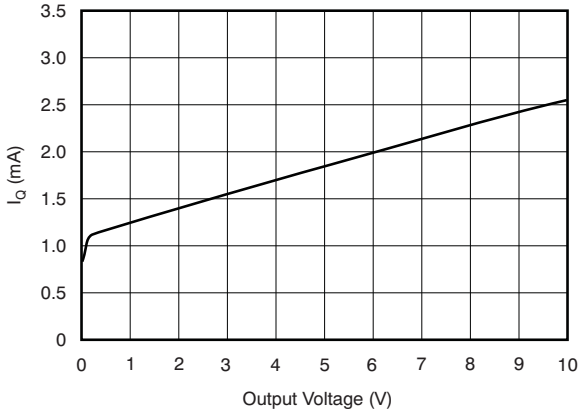


Figure 9.

QUIESCENT CURRENT vs COMMON-MODE VOLTAGE

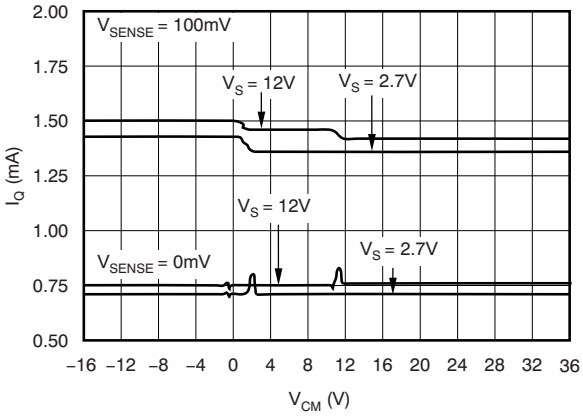


Figure 10.

OUTPUT SHORT-CIRCUIT CURRENT vs SUPPLY VOLTAGE

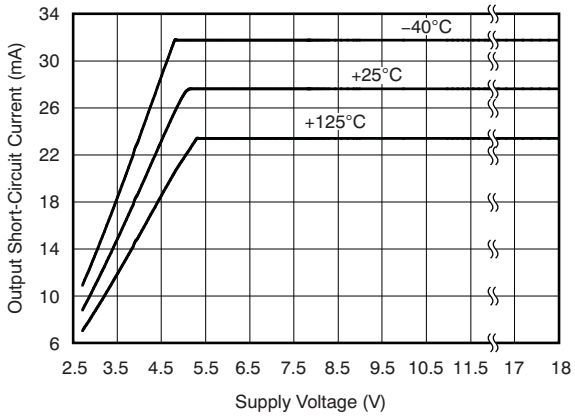


Figure 11.

STEP RESPONSE

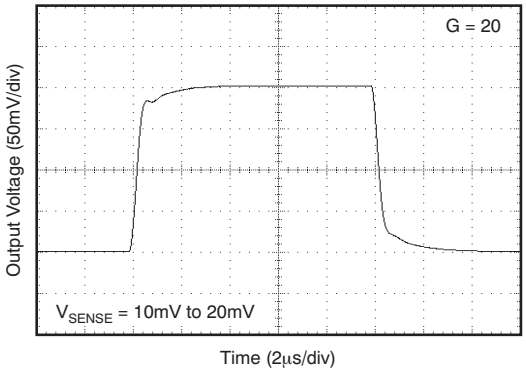


Figure 12.

STEP RESPONSE

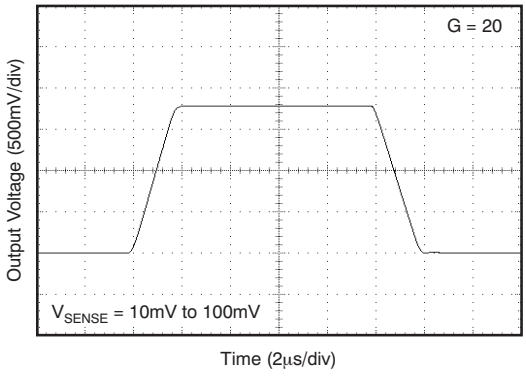


Figure 13.

TYPICAL CHARACTERISTICS (continued)

At T_A = +25°C, V_S = +12V, V_{IN+} = 12V, and V_{SENSE} = 100mV, unless otherwise noted.

STEP RESPONSE

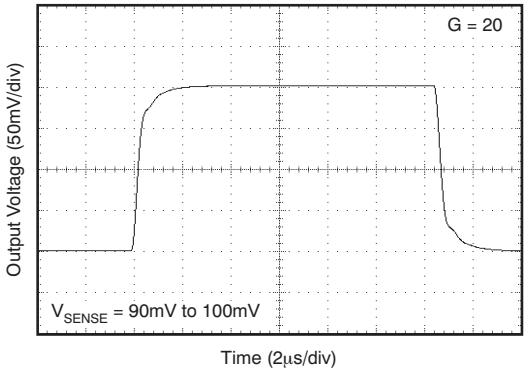


Figure 14.

STEP RESPONSE

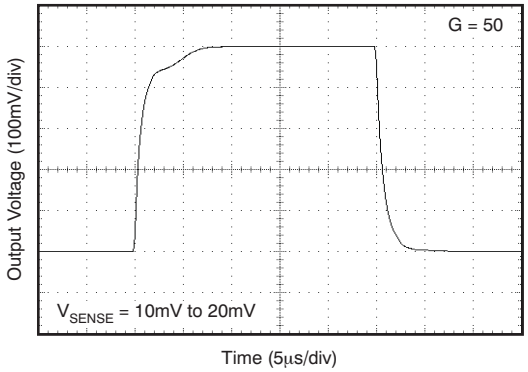


Figure 15.

STEP RESPONSE

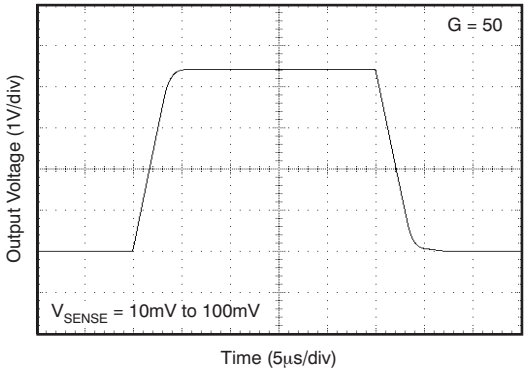


Figure 16.

STEP RESPONSE

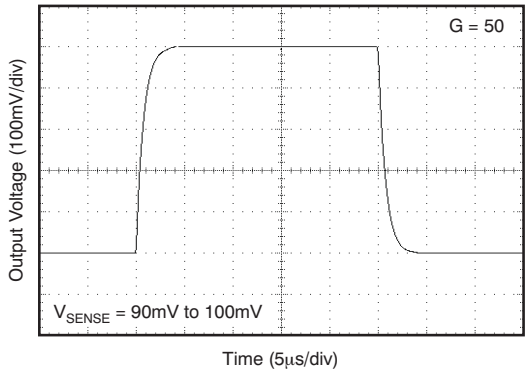


Figure 17.

STEP RESPONSE

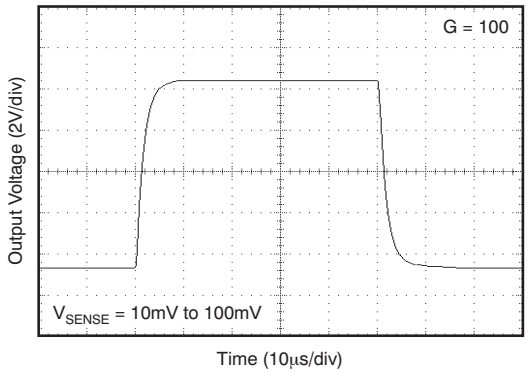


Figure 18.

COMPARATOR V_{OL} vs I_{SINK}

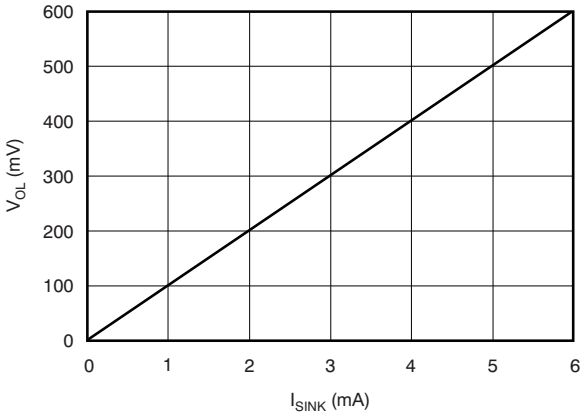


Figure 19.

TYPICAL CHARACTERISTICS (continued)

At T_A = +25°C, V_S = +12V, V_{IN+} = 12V, and V_{SENSE} = 100mV, unless otherwise noted.

COMPARATOR TRIP POINT vs SUPPLY VOLTAGE

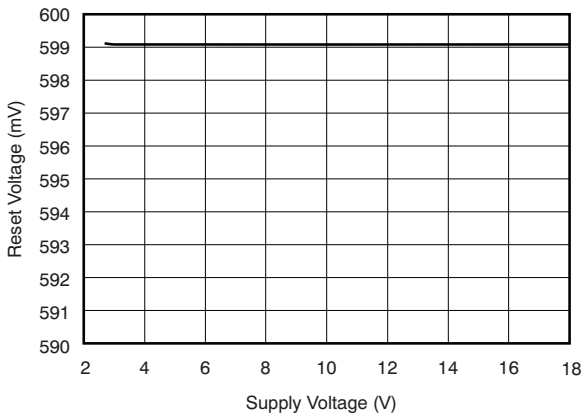


Figure 20.

COMPARATOR TRIP POINT vs TEMPERATURE

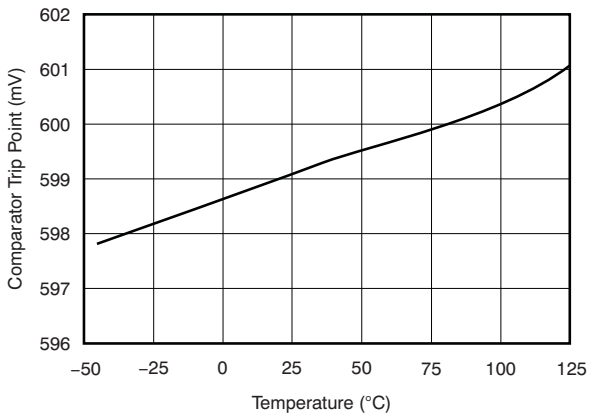


Figure 21.

COMPARATOR PROPAGATION DELAY vs OVERDRIVE VOLTAGE

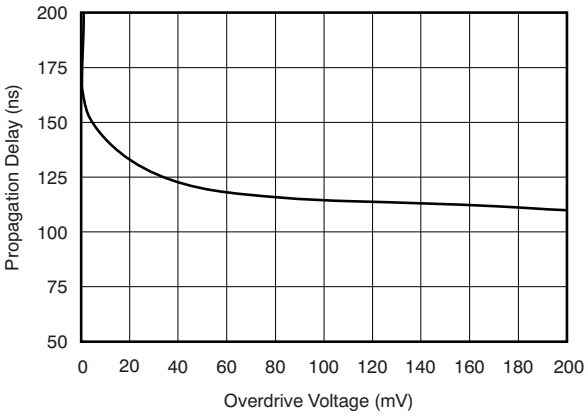


Figure 22.

COMPARATOR RESET VOLTAGE vs SUPPLY VOLTAGE

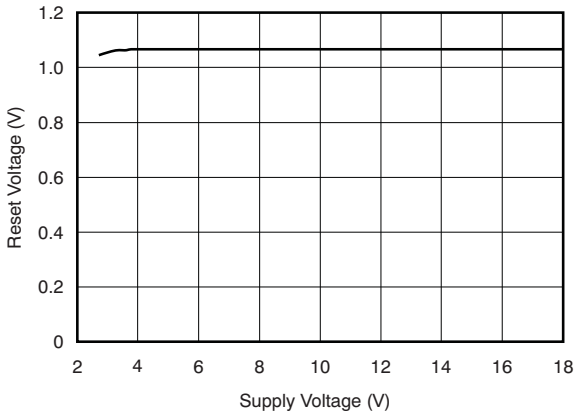


Figure 23.

COMPARATOR PROPAGATION DELAY vs TEMPERATURE

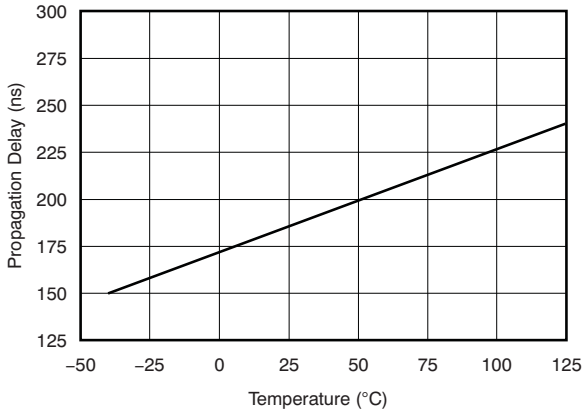


Figure 24.

COMPARATOR PROPAGATION DELAY

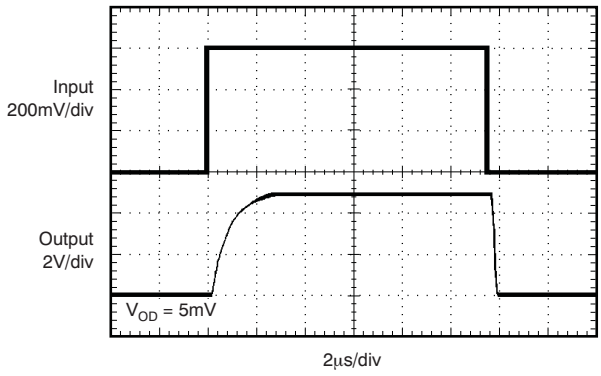


Figure 25.

APPLICATIONS INFORMATION

BASIC CONNECTIONS

Figure 26 shows the basic connections of the INA200, INA201, and INA202. The input pins, V_{IN+} and V_{IN-}, should be connected as closely as possible to the shunt resistor to minimize any resistance in series with the shunt resistance.

Power-supply bypass capacitors are required for stability. Applications with noisy or high-impedance power supplies may require additional decoupling capacitors to reject power-supply noise. Connect bypass capacitors close to the device pins.

POWER SUPPLY

The input circuitry of the INA200, INA201, and INA202 can accurately measure beyond the power-supply voltage, V+. For example, the V+ power supply can be 5V, whereas the load power-supply voltage is up to +80V. The output voltage range of the OUT terminal, however, is limited by the voltages on the power-supply pin.

ACCURACY VARIATIONS AS A RESULT OF V_{SENSE} AND COMMON-MODE VOLTAGE

The accuracy of the INA200, INA201, and INA202 current shunt monitors is a function of two main variables: V_{SENSE} (V_{IN+} – V_{IN-}) and common-mode voltage, V_{CM}, relative to the supply voltage, V_S. V_{CM} is expressed as (V_{IN+} + V_{IN-})/2; however, in practice, V_{CM} is seen as the voltage at V_{IN+} because the voltage drop across V_{SENSE} is usually small.

This section addresses the accuracy of these specific operating regions:

- Normal Case 1: $V_{SENSE} \geq 20mV$, $V_{CM} \geq V_S$
- Normal Case 2: $V_{SENSE} \geq 20mV$, $V_{CM} < V_S$
- Low V_{SENSE} Case 1: $V_{SENSE} < 20mV$, $-16V \leq V_{CM} < 0$
- Low V_{SENSE} Case 2: $V_{SENSE} < 20mV$, $0V \leq V_{CM} \leq V_S$
- Low V_{SENSE} Case 3: $V_{SENSE} < 20mV$, $V_S < V_{CM} \leq 80V$

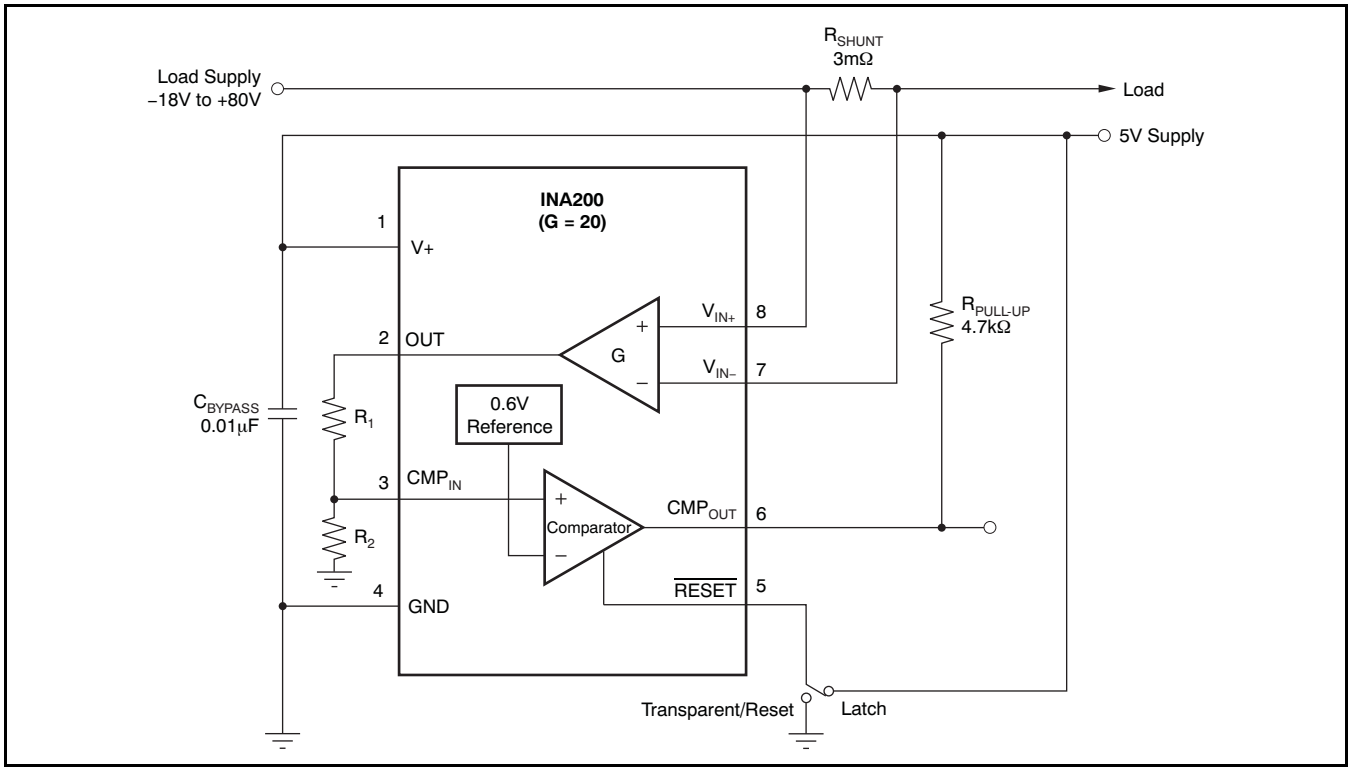


Figure 26. INA200 Basic Connections

Normal Case 1: $V_{SENSE} \geq 20mV$, $V_{CM} \geq V_S$

This region of operation provides the highest accuracy. Here, the input offset voltage is characterized and measured using a two-step method. First, the gain is determined by Equation 1.

$$G = \frac{V_{OUT1} - V_{OUT2}}{100mV - 20mV} \quad (1)$$

where:

V_{OUT1} = Output Voltage with V_{SENSE} = 100mV

V_{OUT2} = Output Voltage with V_{SENSE} = 20mV

Then the offset voltage is measured at V_{SENSE} = 100mV and referred to the input (RTI) of the current shunt monitor, as shown in Equation 2.

$$V_{OS}RTI\ (Referred\text{-}To\text{-}Input) = \left[\frac{V_{OUT1}}{G}\right] - 100mV \quad (2)$$

In the Typical Characteristics, the *Output Error vs Common-Mode Voltage* curve (Figure 7) shows the highest accuracy for the this region of operation. In this plot, V_S = 12V; for $V_{CM} \geq 12V$, the output error is at its minimum. This case is also used to create the $V_{SENSE} \geq 20mV$ output specifications in the Electrical Characteristics table.

Normal Case 2: $V_{SENSE} \geq 20mV$, $V_{CM} < V_S$

This region of operation has slightly less accuracy than Normal Case 1 as a result of the common-mode operating area in which the part functions, as seen in the *Output Error vs Common-Mode Voltage* curve (Figure 7). As noted, for this graph V_S = 12V; for V_{CM} < 12V, the Output Error increases as V_{CM} becomes less than 12V, with a typical maximum error of 0.005% at the most negative V_{CM} = –16V.

Low V_{SENSE} Case 1: $V_{SENSE} < 20mV$, $-16V \leq V_{CM} < 0$; and Low V_{SENSE} Case 3: $V_{SENSE} < 20mV$, $V_S < V_{CM} \leq 80V$

Although the INA200 family of devices are not designed for accurate operation in either of these regions, some applications are exposed to these conditions. For example, when monitoring power supplies that are switched on and off while V_S is still applied to the INA200, INA201, or INA202, it is important to know what the behavior of the devices will be in these regions.

As V_{SENSE} approaches 0mV, in these V_{CM} regions, the device output accuracy degrades. A larger-than-normal offset can appear at the current shunt monitor output with a typical maximum value of V_{OUT} = 300mV for V_{SENSE} = 0mV. As V_{SENSE} approaches 20mV, V_{OUT} returns to the expected output value with accuracy as specified in the Electrical Characteristics. Figure 27 illustrates this effect using the INA202 (Gain = 100).

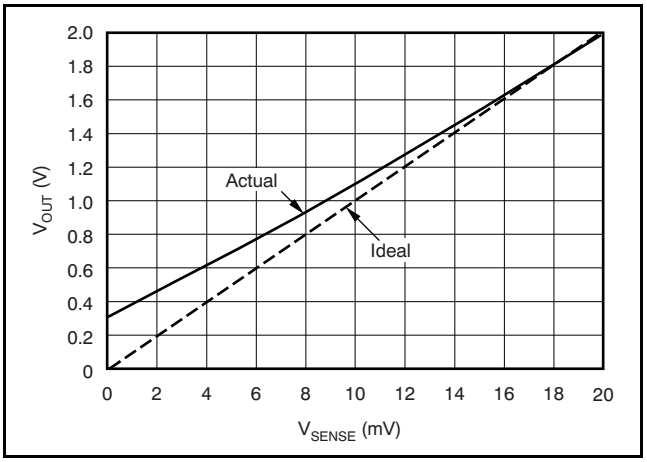
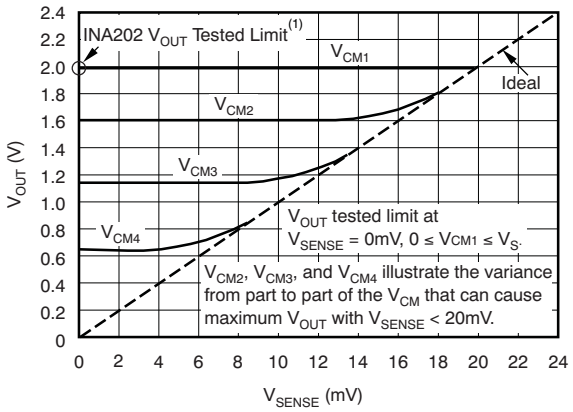


Figure 27. Example for Low V_{SENSE} Cases 1 and 3 (INA202, Gain = 100)

Low V_{SENSE} Case 2: $V_{SENSE} < 20mV$, $0V \leq V_{CM} \leq V_S$

This region of operation is the least accurate for the INA200 family. To achieve the wide input common-mode voltage range, these devices use two op amp front ends in parallel. One op amp front end operates in the positive input common-mode voltage range, and the other in the negative input region. For this case, neither of these two internal amplifiers dominates and overall loop gain is very low. Within this region, V_{OUT} approaches voltages close to linear operation levels for Normal Case 2. This deviation from linear operation becomes greatest the closer V_{SENSE} approaches 0V. Within this region, as V_{SENSE} approaches 20mV, device operation is closer to that described by Normal Case 2. Figure 28 illustrates this behavior for the INA202. The V_{OUT} maximum peak for this case is tested by maintaining a constant V_S, setting V_{SENSE} = 0mV and sweeping V_{CM} from 0V to V_S. The exact V_{CM} at which V_{OUT} peaks during this test varies from part to part, but the V_{OUT} maximum peak is tested to be less than the specified V_{OUT} tested limit.



NOTE: (1) INA200 V_{OUT} Tested Limit = 0.4V. INA201 V_{OUT} Tested Limit = 1V.

Figure 28. Example for Low V_{SENSE} Case 2 (INA202, Gain = 100)

SELECTING R_S

The value chosen for the shunt resistor, R_S, depends on the application and is a compromise between small-signal accuracy and maximum permissible voltage loss in the measurement line. High values of R_S provide better accuracy at lower currents by minimizing the effects of offset, while low values of R_S minimize voltage loss in the supply line. For most applications, best performance is attained with an R_S value that provides a full-scale shunt voltage range of 50mV to 100mV. Maximum input voltage for accurate measurements is 500mV.

TRANSIENT PROTECTION

The –16V to +80V common-mode range of the INA200, INA201, and INA202 is ideal for withstanding automotive fault conditions ranging from 12V battery reversal up to +80V transients, since no additional protective components are needed up to those levels. In the event that the INA200, INA201, and INA202 are exposed to transients on the inputs in excess of their ratings, then external transient absorption with semiconductor transient absorbers (such as zeners) will be necessary. Use of MOVs or VDRs is not recommended except when they are used in addition to a semiconductor transient absorber. Select the transient absorber such that it will never allow the INA200, INA201, and INA202 to be exposed to transients greater than +80V (that is, allow for transient absorber tolerance, as well as additional voltage due to transient absorber dynamic impedance). Despite the use of internal zener-type ESD protection, the INA200, INA201, and INA202 do not lend themselves to using external resistors in series with the inputs since the internal gain resistors can vary up to ±30%. (If gain accuracy is not important, then resistors can be added in series with the INA200, INA201, and INA202 inputs with two equal resistors on each input.)

OUTPUT VOLTAGE RANGE

The output of the INA200, INA201, and INA202 is accurate within the output voltage swing range set by the power supply pin, V+. This performance is best illustrated when using the INA202 (a gain of 100 version), where a 100mV full-scale input from the shunt resistor requires an output voltage swing of +10V, and a power-supply voltage sufficient to achieve +10V on the output.

INPUT FILTERING

An obvious and straightforward location for filtering is at the output of the INA200, INA201, and INA202 series; however, this location negates the advantage of the low output impedance of the internal buffer. The only other option for filtering is at the input pins of the INA200, INA201, and INA202, which is complicated by the internal 5kΩ + 30% input impedance; this is illustrated in Figure 29. Using the lowest possible resistor values minimizes both the initial shift in gain and effects of tolerance. The effect on initial gain is given by Equation 3:

$$\text{Gain Error \%} = 100 - \left(100 \times \frac{5k\Omega}{5k\Omega + R_{FILT}}\right) \quad (3)$$

Total effect on gain error can be calculated by replacing the 5kΩ term with 5kΩ – 30%, (or 3.5kΩ) or 5kΩ + 30% (or 6.5kΩ). The tolerance extremes of R_{FILT} can also be inserted into the equation. If a pair of 100Ω 1% resistors are used on the inputs, the initial gain error will be 1.96%. Worst-case tolerance conditions will always occur at the lower excursion of the internal 5kΩ resistor (3.5kΩ), and the higher excursion of R_{FILT} – 3% in this case.

Note that the specified accuracy of the INA200, INA201, and INA202 must then be combined in addition to these tolerances. While this discussion treated accuracy worst-case conditions by combining the extremes of the resistor values, it is appropriate to use geometric mean or root sum square calculations to total the effects of accuracy variations.

COMPARATOR

The INA200, INA201, and INA202 devices incorporate an open-drain comparator. This comparator typically has 2mV of offset and a 1.3μs (typical) response time. The output of the comparator latches and is reset through the $\overline{\text{RESET}}$ pin; see Figure 30.

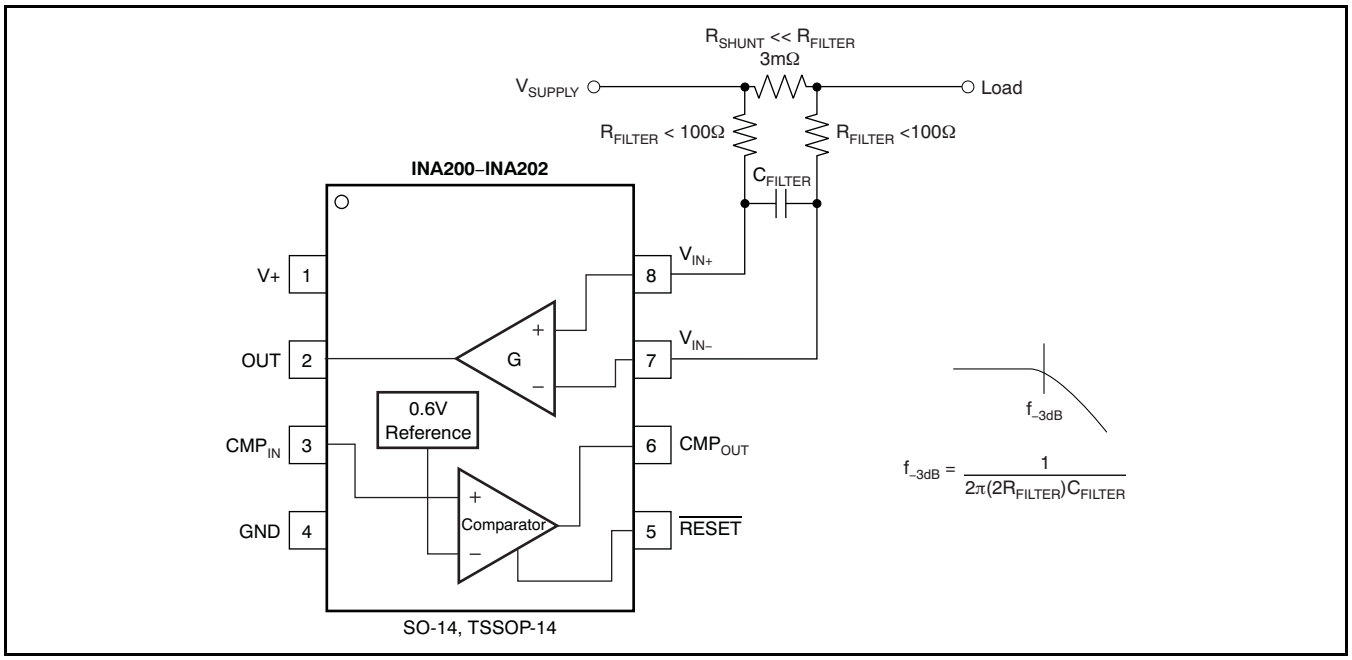


Figure 29. Input Filter (Gain Error—1.5% to –2.2%)

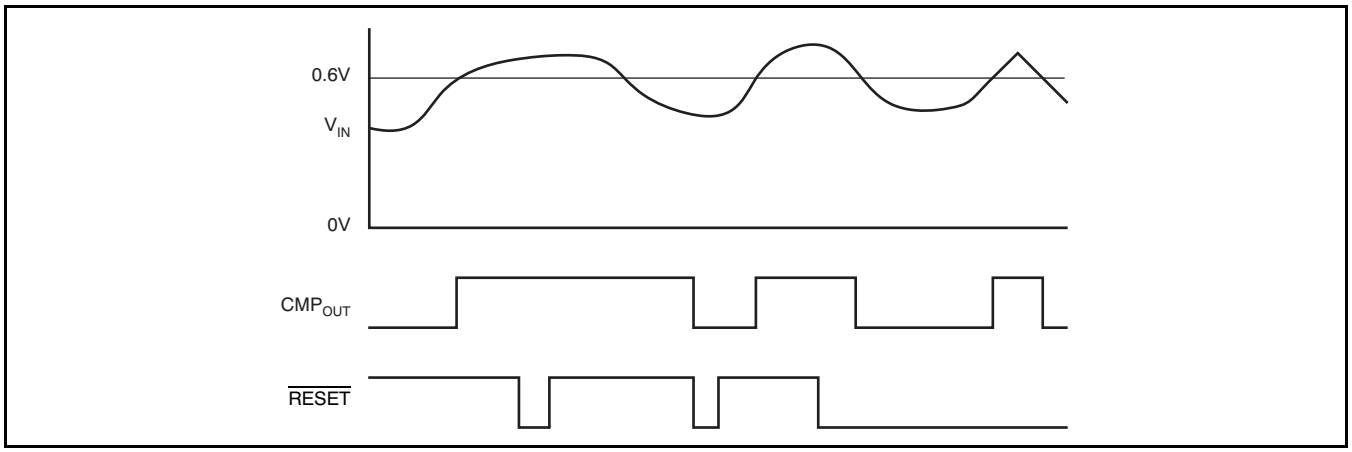
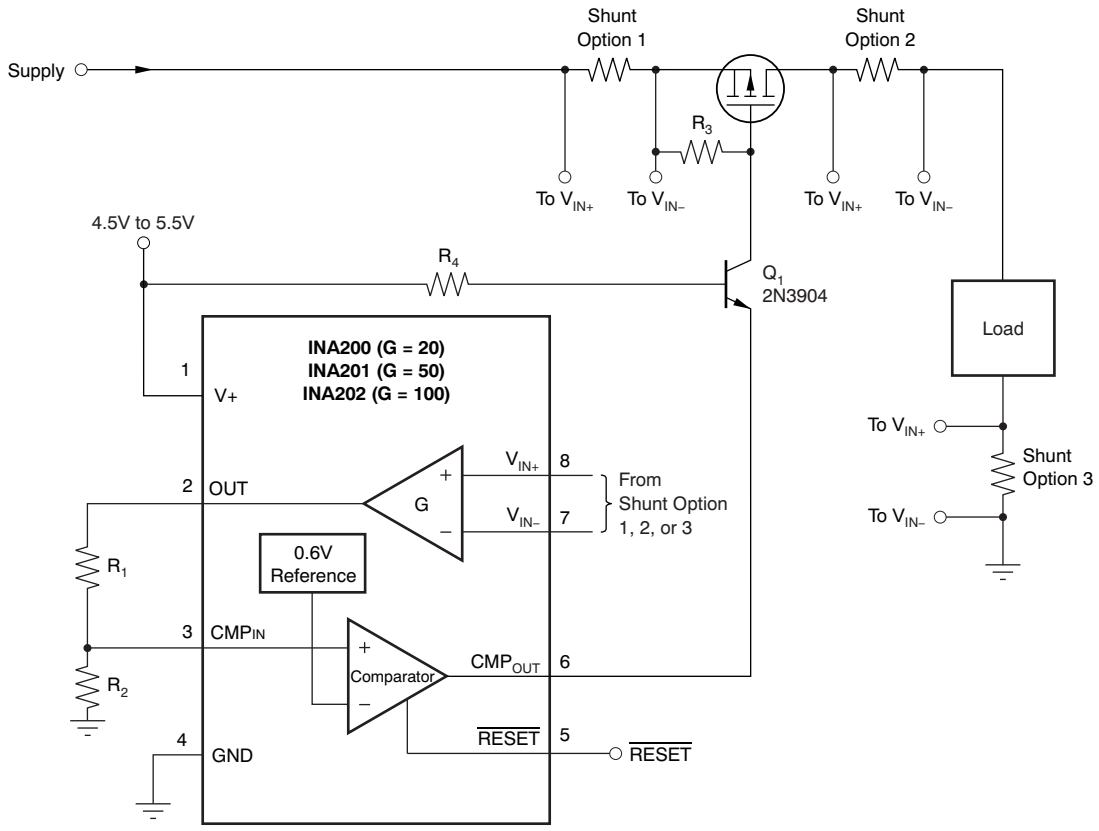
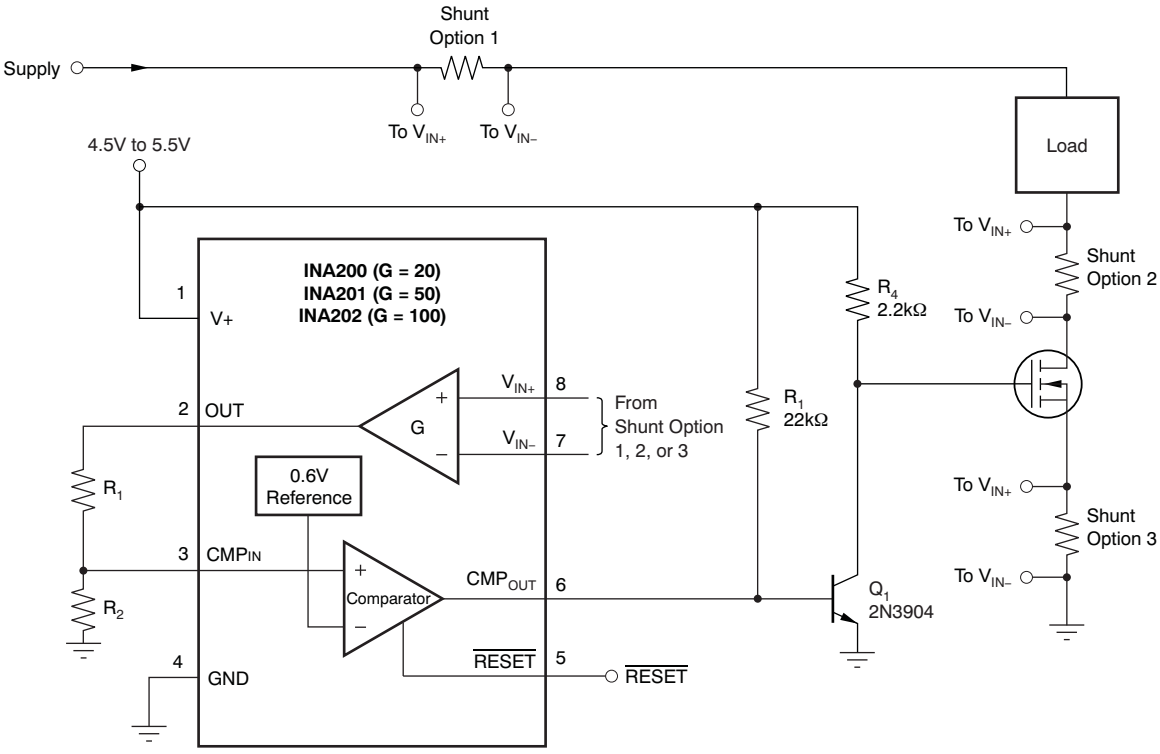


Figure 30. Comparator Latching Capability



NOTE: Q_1 cascodes the comparator output to drive a high-side FET (the 2N3904 shown is good up to 60V). The shunt could be located in any one of the three locations shown. The latching capability should be used in shutdown applications to prevent oscillation at the trip point.

Figure 31. High-Side Switch Over-Current Shutdown



NOTE: In this case, Q_1 is used to invert the comparator output.

Figure 32. Low-Side Switch Over-Current Shutdown

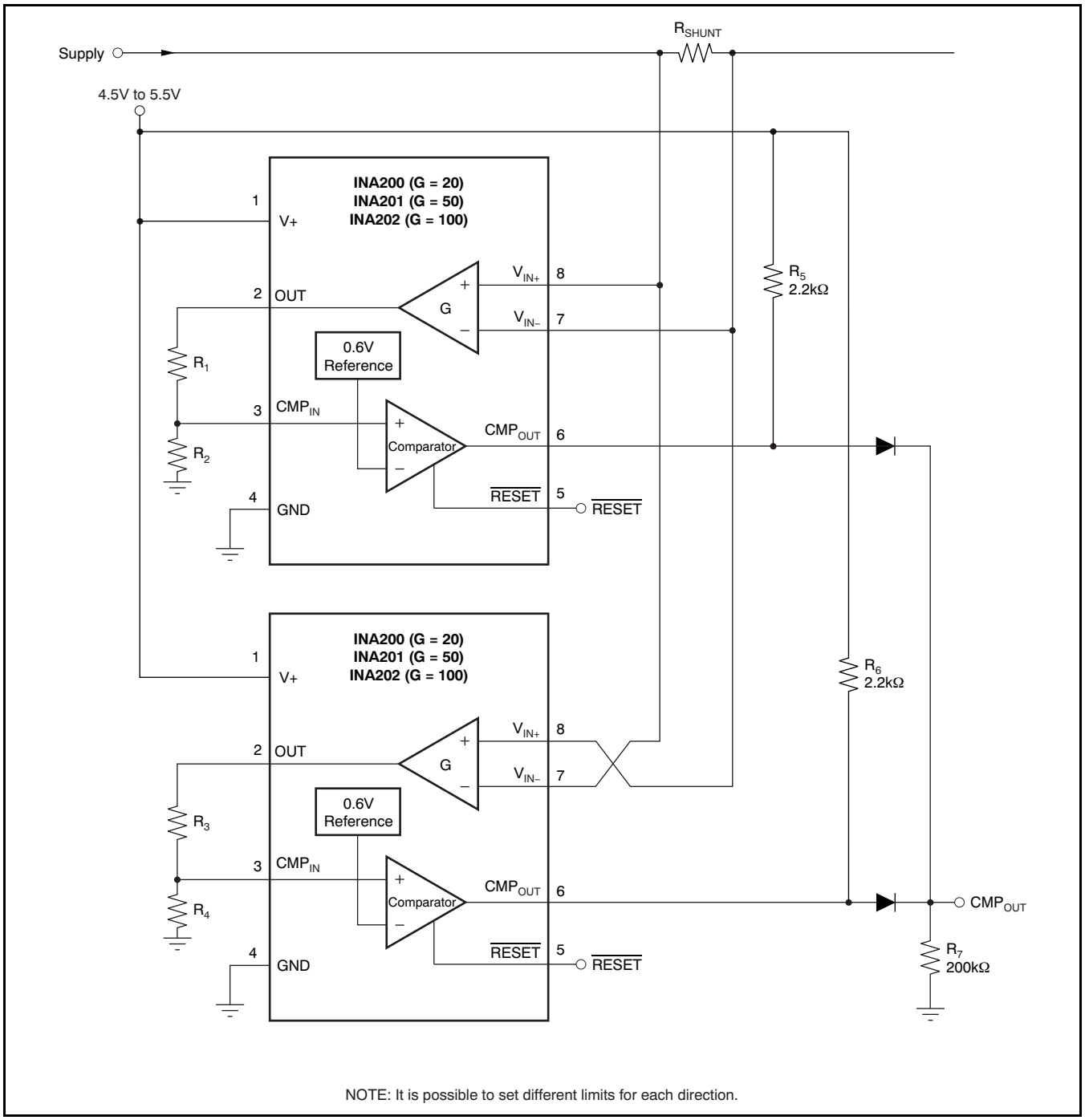


Figure 33. Bidirectional Over-Current Comparator

REVISION HISTORY

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (October, 2007) to Revision C	Page
• Changed title of data sheet	1
• Updated document format to current standards	1
• Revised front-page figure	1

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
INA200AID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 200A	Samples
INA200AIDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 200A	Samples
INA200AIDGKR	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	BQH	Samples
INA200AIDGKRG4	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	BQH	Samples
INA200AIDGKT	ACTIVE	VSSOP	DGK	8	250	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	BQH	Samples
INA200AIDGKTG4	ACTIVE	VSSOP	DGK	8	250	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	BQH	Samples
INA200AIDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 200A	Samples
INA200AIDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 200A	Samples
INA201AID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 201A	Samples
INA201AIDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 201A	Samples
INA201AIDGKR	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU | CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	BQJ	Samples
INA201AIDGKRG4	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	BQJ	Samples
INA201AIDGKT	ACTIVE	VSSOP	DGK	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU | CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	BQJ	Samples
INA201AIDGKTG4	ACTIVE	VSSOP	DGK	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	BQJ	Samples
INA201AIDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 201A	Samples
INA201AIDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 201A	Samples
INA202AID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 202A	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
INA202AIDGKR	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU | CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	BQL	Samples
INA202AIDGKT	ACTIVE	VSSOP	DGK	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU | CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	BQL	Samples
INA202AIDGKTG4	ACTIVE	VSSOP	DGK	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	BQL	Samples
INA202AIDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 202A	Samples
INA202AIDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA 202A	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

OTHER QUALIFIED VERSIONS OF INA200, INA201, INA202 :

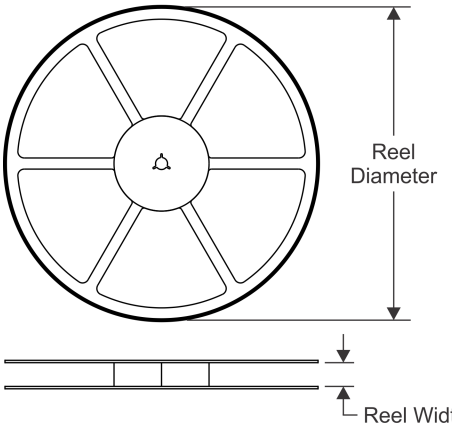
- Automotive: INA200-Q1, INA201-Q1, INA202-Q1

NOTE: Qualified Version Definitions:

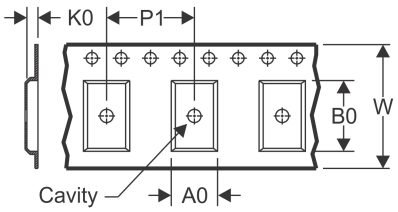
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION

REEL DIMENSIONS

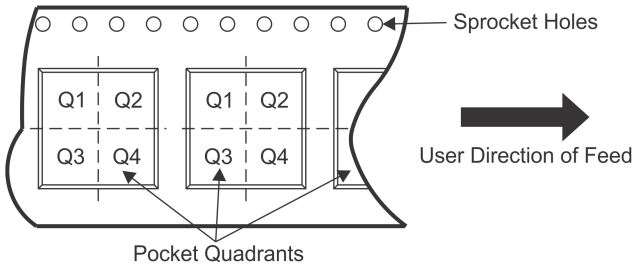


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

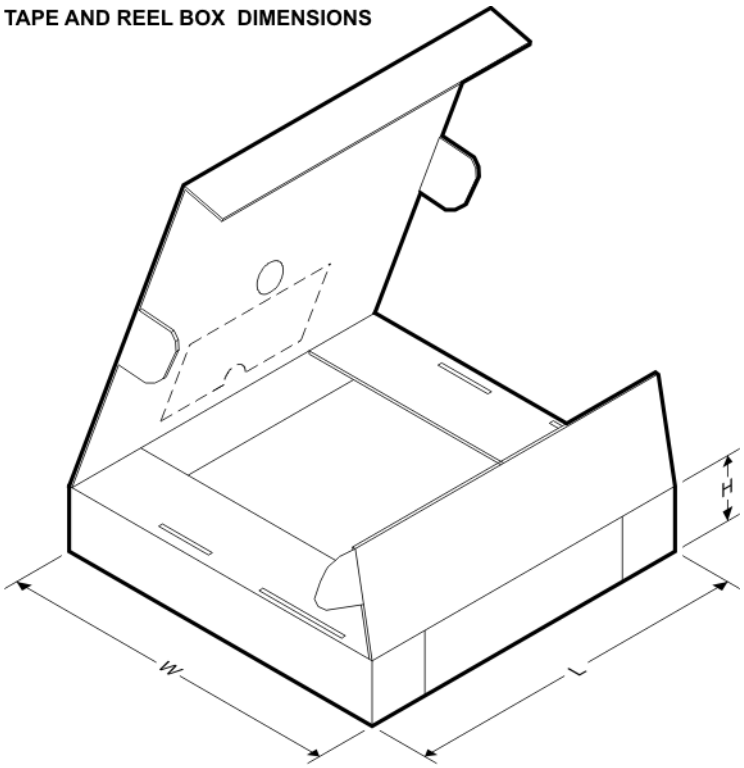
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
INA200AIDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
INA200AIDGKT	VSSOP	DGK	8	250	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
INA200AIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
INA201AIDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
INA201AIDGKT	VSSOP	DGK	8	250	180.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
INA201AIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
INA202AIDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
INA202AIDGKT	VSSOP	DGK	8	250	180.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
INA202AIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

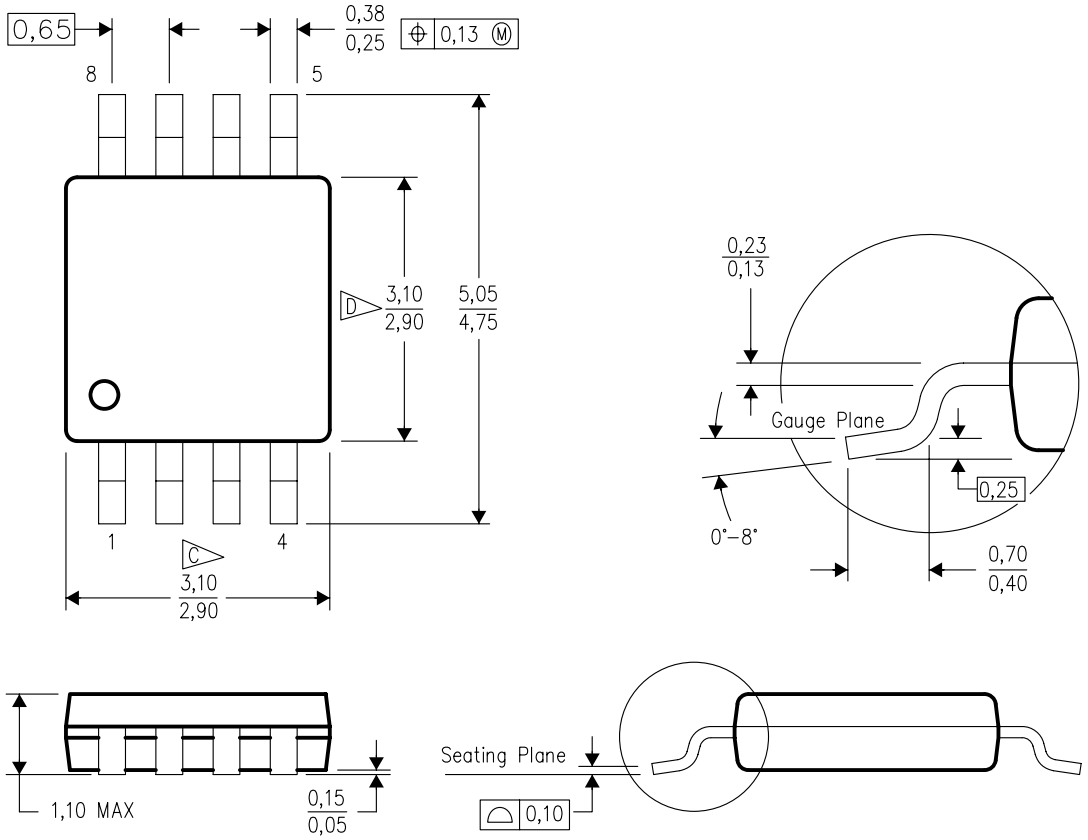
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
INA200AIDGKR	VSSOP	DGK	8	2500	366.0	364.0	50.0
INA200AIDGKT	VSSOP	DGK	8	250	366.0	364.0	50.0
INA200AIDR	SOIC	D	8	2500	367.0	367.0	35.0
INA201AIDGKR	VSSOP	DGK	8	2500	367.0	367.0	35.0
INA201AIDGKT	VSSOP	DGK	8	250	210.0	185.0	35.0
INA201AIDR	SOIC	D	8	2500	367.0	367.0	35.0
INA202AIDGKR	VSSOP	DGK	8	2500	367.0	367.0	35.0
INA202AIDGKT	VSSOP	DGK	8	250	210.0	185.0	35.0
INA202AIDR	SOIC	D	8	2500	367.0	367.0	35.0

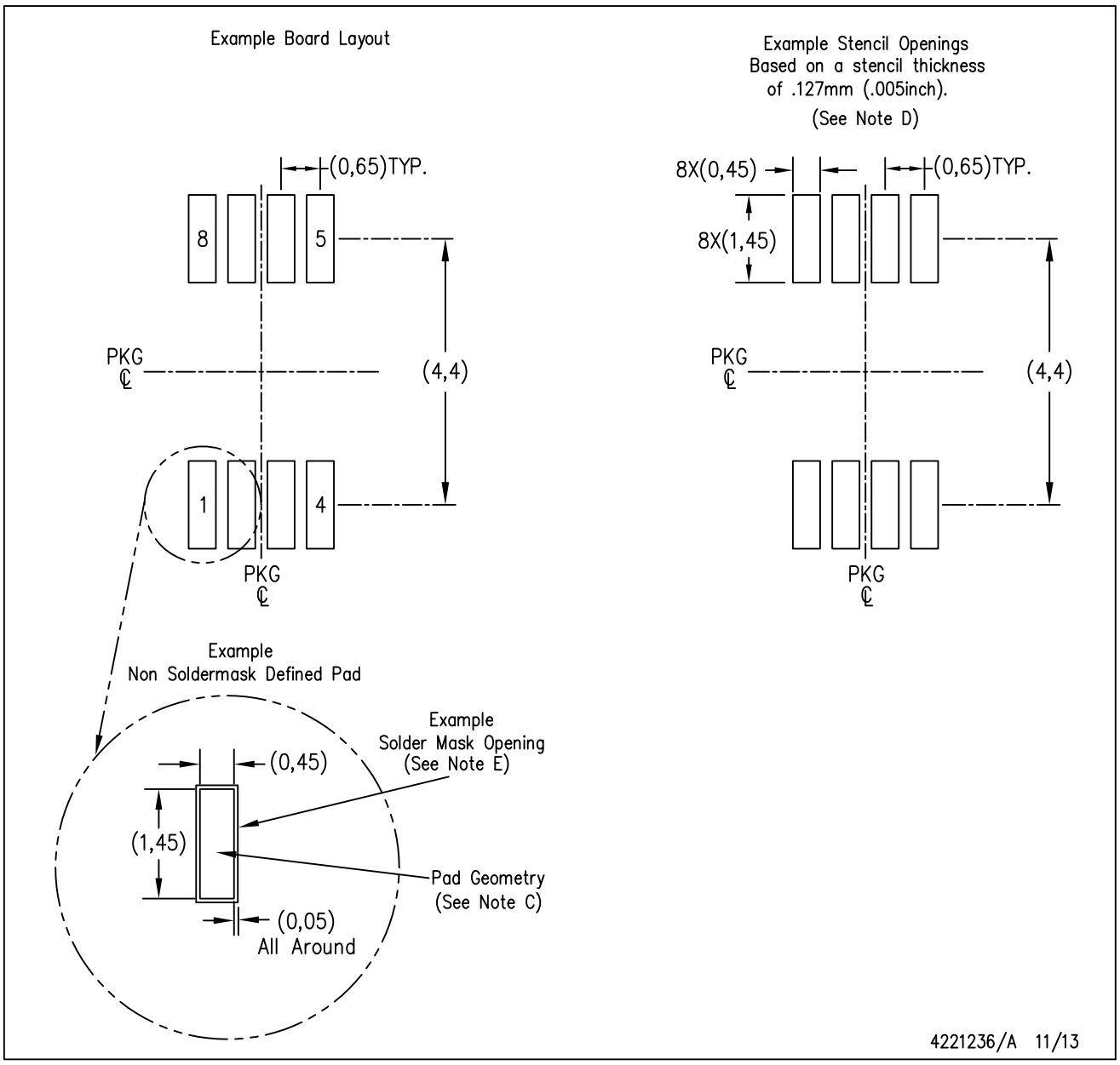
DGK (S–PDSO–G8) PLASTIC SMALL–OUTLINE PACKAGE



4073329/E 05/06

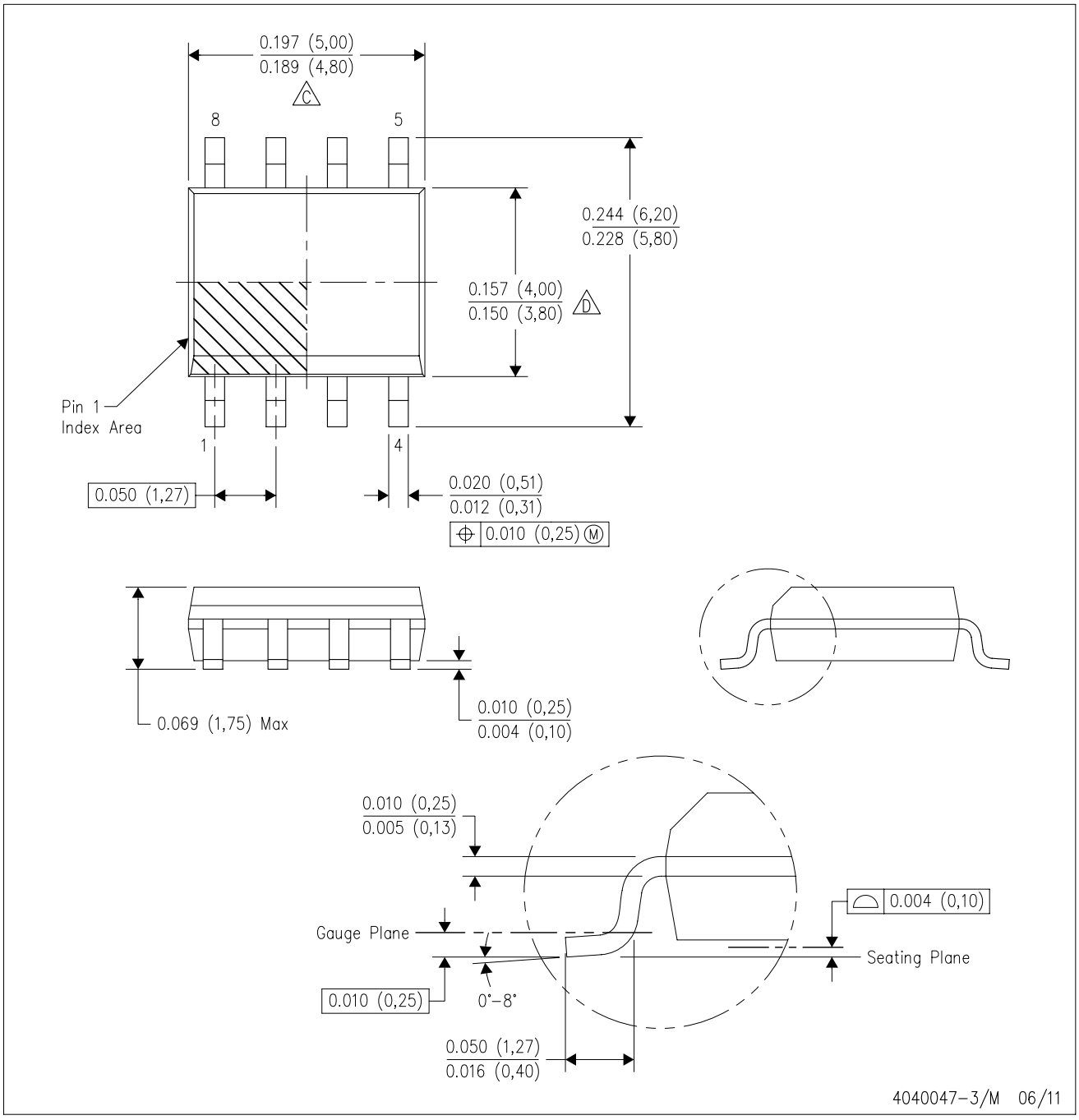
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
E. Falls within JEDEC MO–187 variation AA, except interlead flash.

DGK (S–PDSO–G8) PLASTIC SMALL OUTLINE PACKAGE



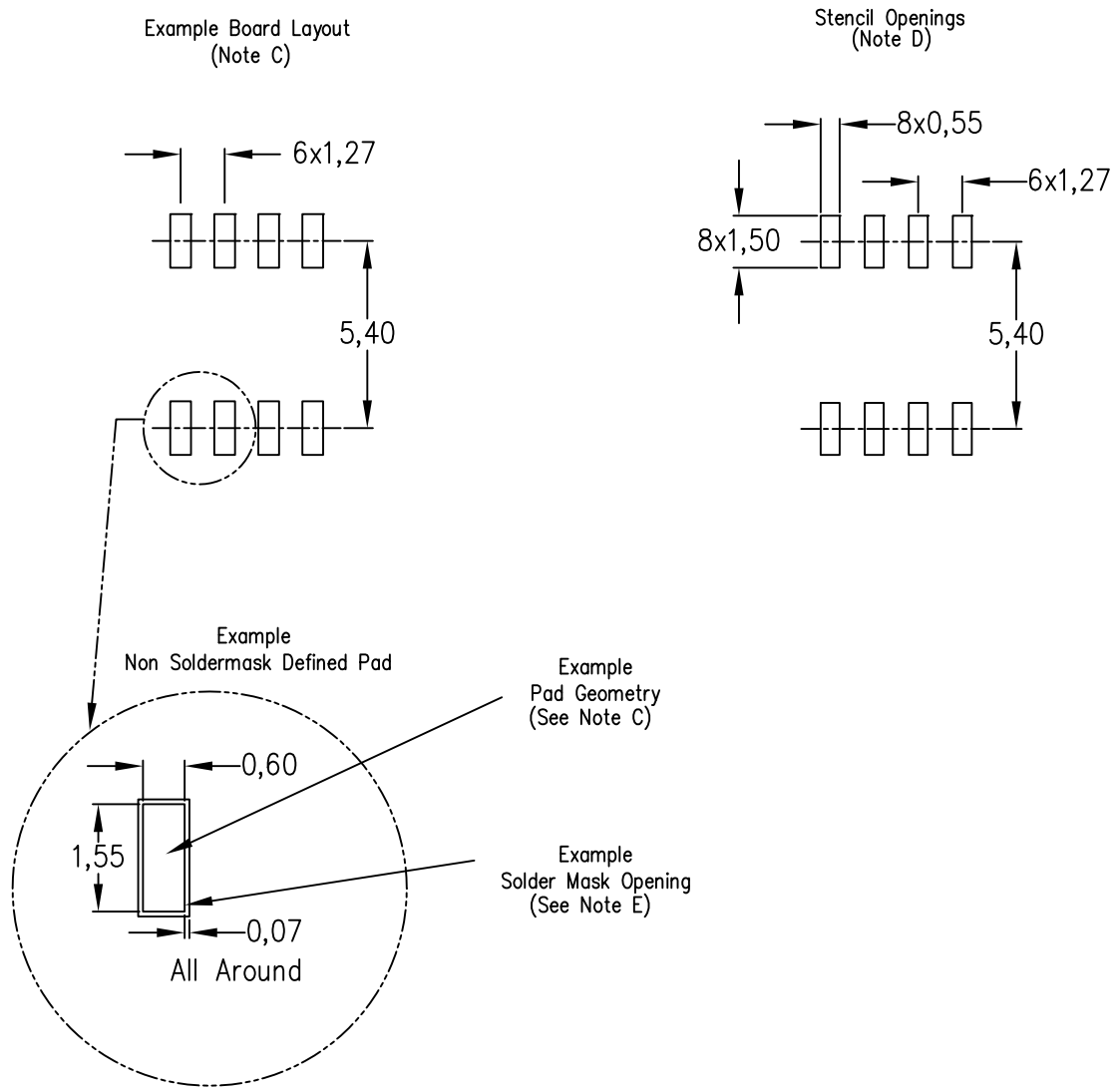
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

D (R–PDSO–G8) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AA.

D (R–PDSO–G8) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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